

BTA316-800ET

16 A three-quadrant high commutation triac

Rev. 01 — 29 March 2010

Product data sheet

1. Product profile

1.1 General description

Planar passivated, new generation, high commutation, high operating junction temperature, three-quadrant triac in a SOT78 plastic package.

1.2 Features and benefits

- Hi-Com triac with maximum false trigger immunity
- High operating junction temperature
- Planar passivated
- Sensitive gate for direct triggering from microcontrollers and logic ICs
- Triggering in three quadrants only

1.3 Applications

- Applications subject to high temperature
- Electronic thermostats, heating and cooking controls
- High power motor controls in washing machines and vacuum cleaners
- Refrigeration and air-conditioner compressor controls

1.4 Quick reference data

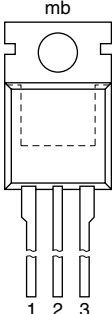
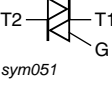
Table 1. Quick reference

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	800	V
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{\text{j(init)}} = 25\text{ °C}$; $t_{\text{p}} = 20\text{ ms}$; see Figure 4 and 5	-	-	140	A
T_{j}	junction temperature		-	-	150	°C
$I_{\text{T(RMS)}}$	RMS on-state current	full sine wave; $T_{\text{mb}} \leq 126\text{ °C}$; see Figure 3 , 1 and 2	-	-	16	A
Static characteristics						
I_{GT}	gate trigger current	$V_{\text{D}} = 12\text{ V}$; $I_{\text{T}} = 0.1\text{ A}$; T2+ G+; $T_{\text{j}} = 25\text{ °C}$; see Figure 7	-	-	10	mA
		$V_{\text{D}} = 12\text{ V}$; $I_{\text{T}} = 0.1\text{ A}$; T2+ G-; $T_{\text{j}} = 25\text{ °C}$; see Figure 7	-	-	10	mA
		$V_{\text{D}} = 12\text{ V}$; $I_{\text{T}} = 0.1\text{ A}$; T2- G-; $T_{\text{j}} = 25\text{ °C}$; see Figure 7	-	-	10	mA



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		
2	T2	main terminal 2		
3	G	gate		
mb	T2	mounting base; main terminal 2		

SOT78 (TO-220AB)

3. Ordering information

Table 3. Ordering information

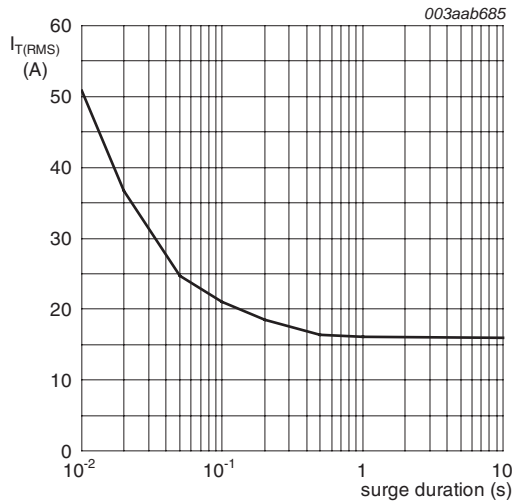
Type number	Package		Version
	Name	Description	
BTA316-800ET	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 126\text{ °C}$; see Figure 3, 1 and 2	-	16	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 20\text{ ms}$; see Figure 4 and 5	-	140	A
		full sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 16.7\text{ ms}$	-	150	A
I^2t	I^2t for fusing	$t_p = 10\text{ ms}$; sine-wave pulse	-	98	A ² s
di_T/dt	rate of rise of on-state current	$I_T = 20\text{ A}$; $I_G = 0.2\text{ A}$; $di_G/dt = 0.2\text{ A}/\mu\text{s}$	-	100	A/ μs
I_{GM}	peak gate current		-	2	A
P_{GM}	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
T_{stg}	storage temperature		-40	150	°C
T_j	junction temperature		-	150	°C



$f = 50 \text{ Hz}; T_{mb} = 126 \text{ }^\circ\text{C}$

Fig 1. RMS on-state current as a function of surge duration; maximum values

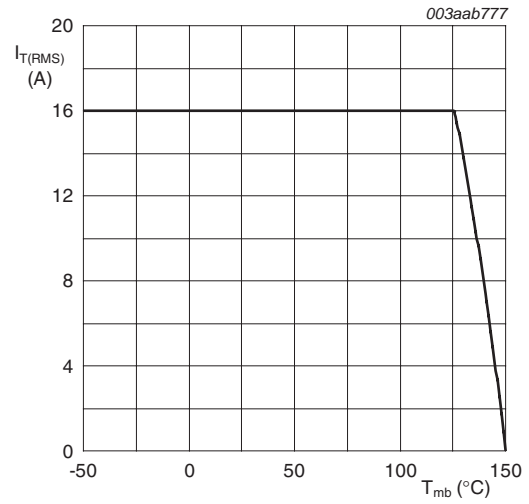
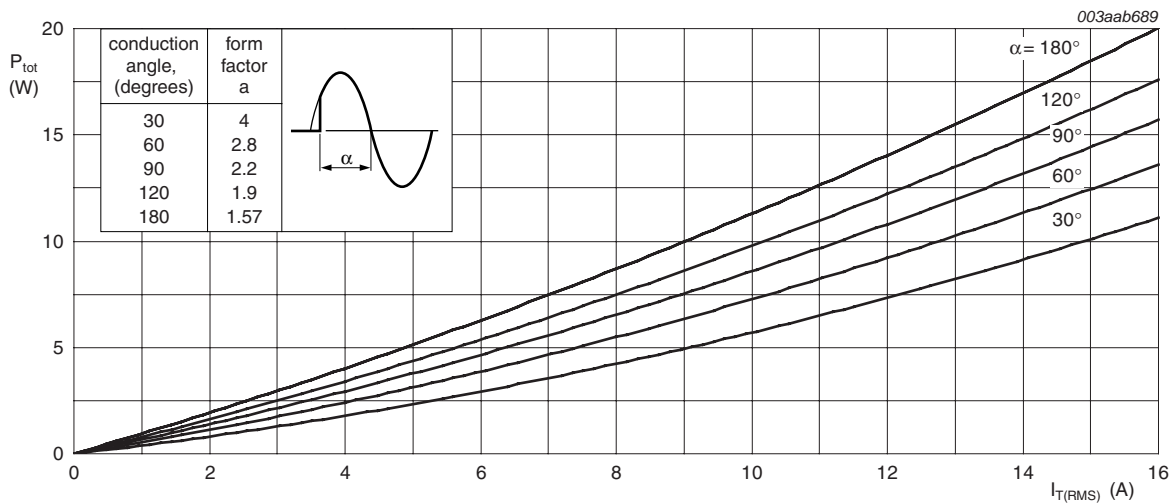


Fig 2. RMS on-state current as a function of mounting base temperature; maximum values



$\alpha = \text{conduction angle}$

Fig 3. Total power dissipation as a function of RMS on-state current; maximum values

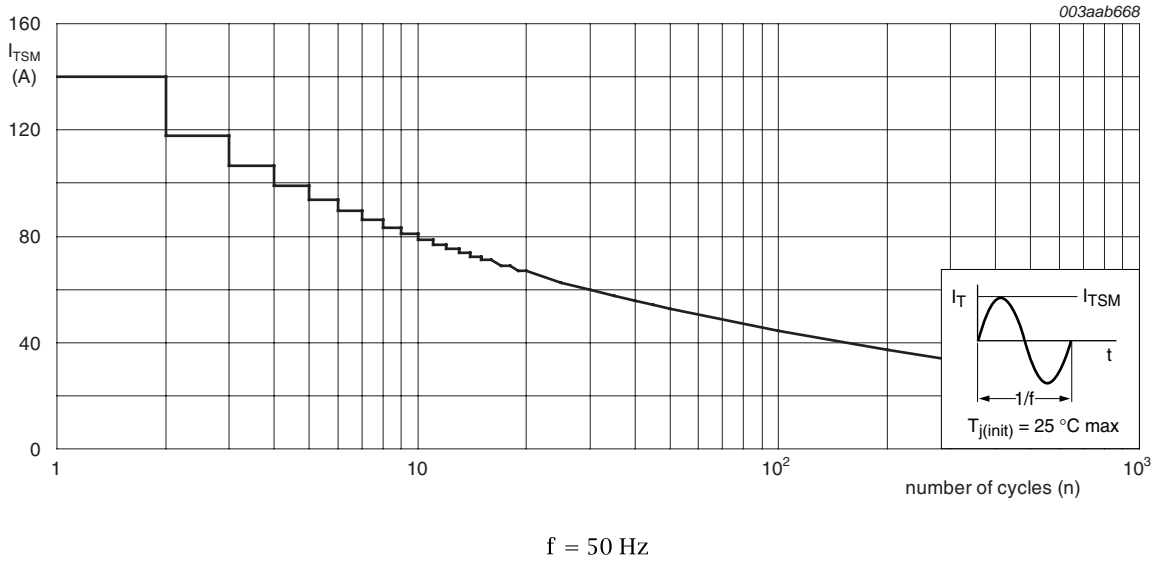


Fig 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

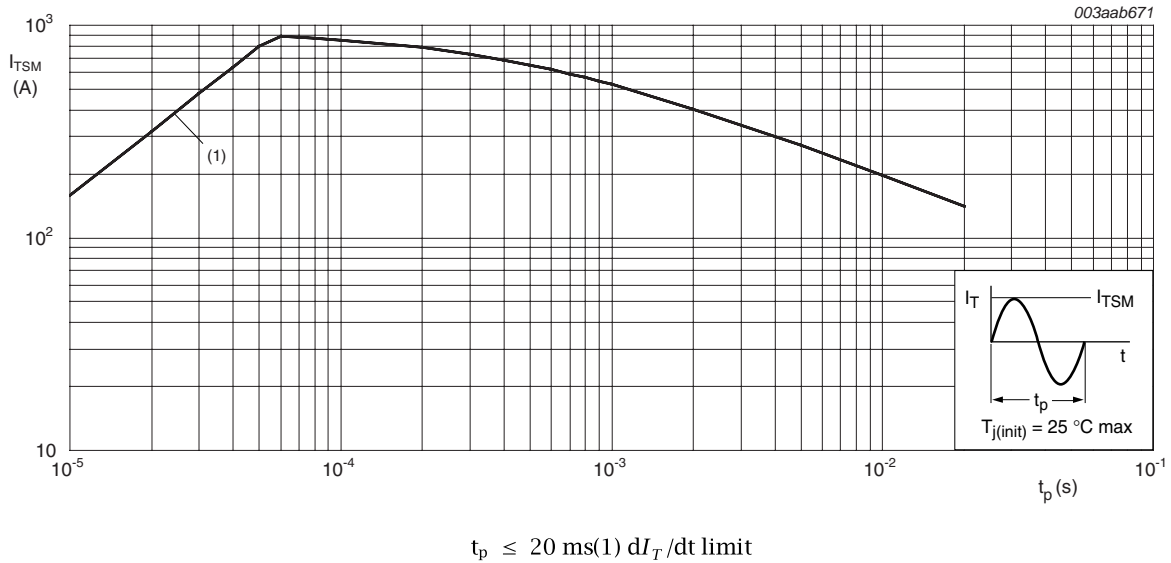
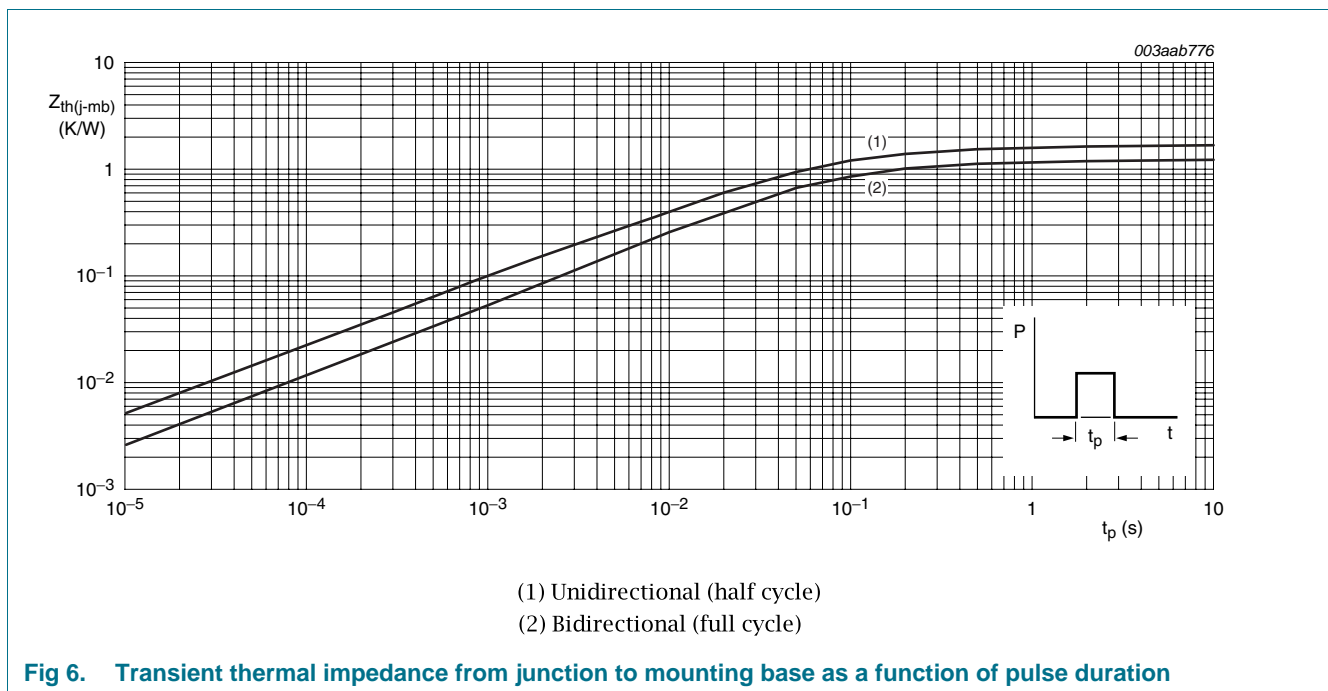


Fig 5. Non-repetitive peak on-state current as a function of pulse duration; maximum values

5. Thermal characteristics

Table 5. Thermal characteristics

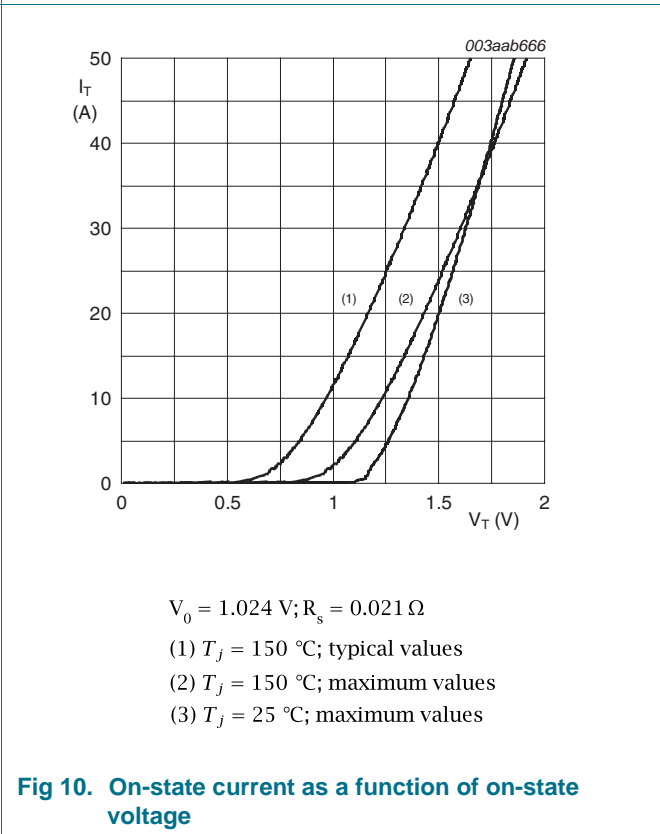
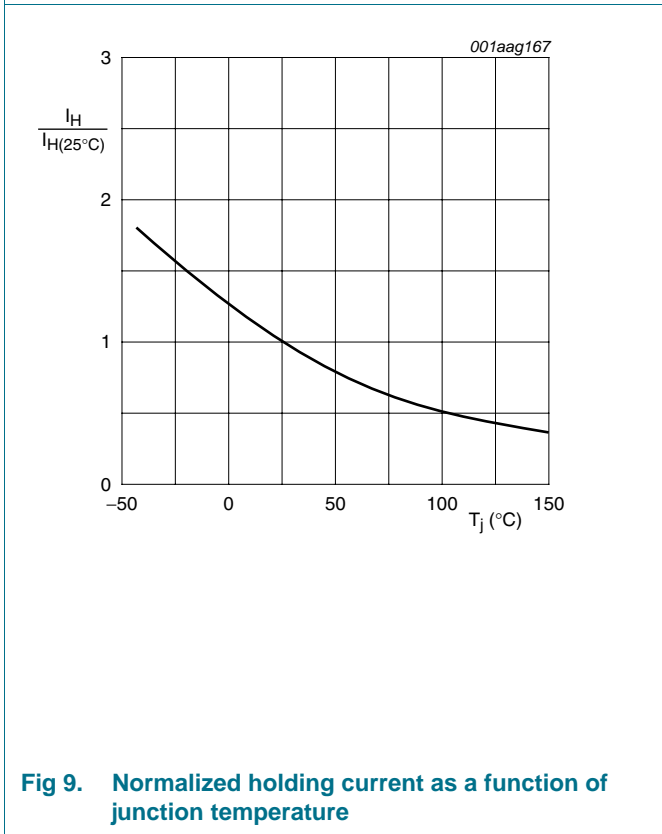
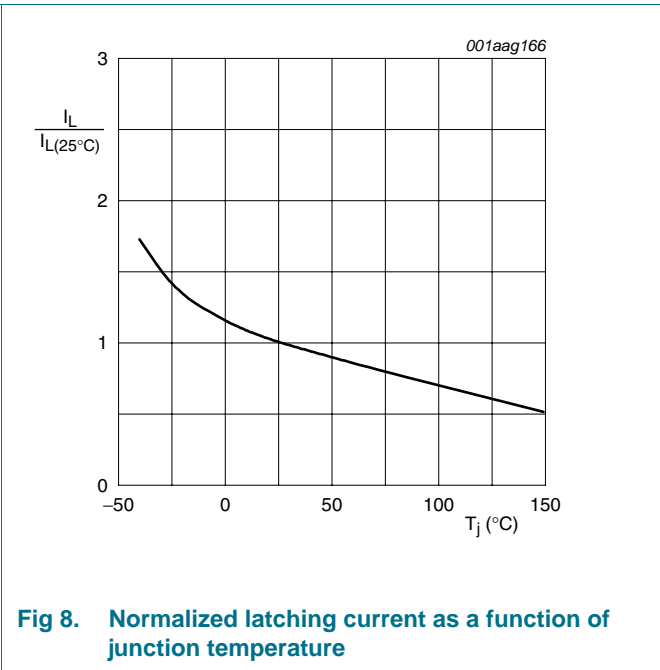
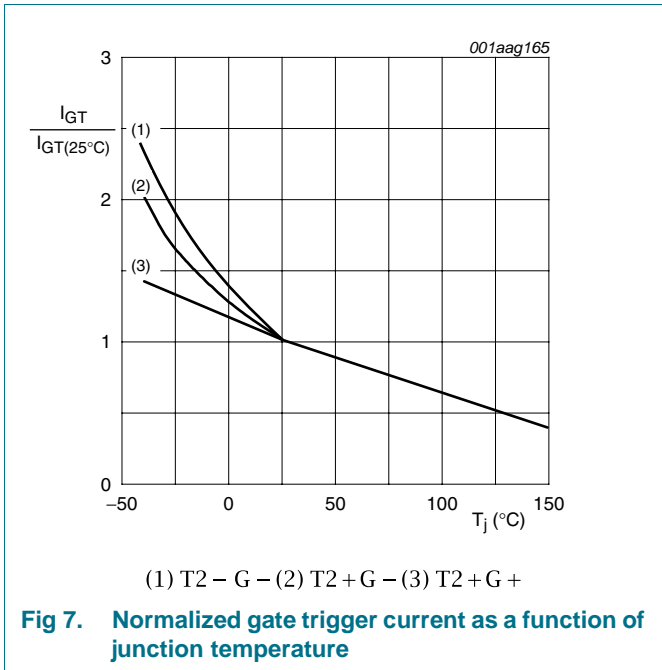
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	full cycle; see Figure 6	-	-	1.2	K/W
		half cycle; see Figure 6	-	-	1.7	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W



6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G+; $T_j = 25\text{ °C}$; see Figure 7	-	-	10	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ °C}$; see Figure 7	-	-	10	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G-; $T_j = 25\text{ °C}$; see Figure 7	-	-	10	mA
I_L	latching current	$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2+ G+; $T_j = 25\text{ °C}$; see Figure 8	-	-	25	mA
		$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ °C}$; see Figure 8	-	-	30	mA
		$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2- G-; $T_j = 25\text{ °C}$; see Figure 8	-	-	30	mA
I_H	holding current	$V_D = 12\text{ V}$; $T_j = 25\text{ °C}$; see Figure 9	-	-	15	mA
V_T	on-state voltage	$I_T = 18\text{ A}$; $T_j = 25\text{ °C}$; see Figure 10	-	1.3	1.5	V
V_{GT}	gate trigger voltage	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 25\text{ °C}$; see Figure 11	-	0.8	1.5	V
		$V_D = 400\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 150\text{ °C}$; see Figure 11	0.25	-	-	V
I_D	off-state current	$V_D = 800\text{ V}$; $T_j = 150\text{ °C}$	-	0.4	2	mA
Dynamic characteristics						
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}$; $T_j = 150\text{ °C}$; exponential waveform	20	-	-	V/ μ s
dl_{com}/dt	rate of change of commutating current	$V_D = 400\text{ V}$; $T_j = 150\text{ °C}$; $I_{T(RMS)} = 16\text{ A}$; $dV_{com}/dt = 10\text{ V}/\mu\text{s}$; gate open circuit	1.2	-	-	A/ms
		$V_D = 400\text{ V}$; $T_j = 150\text{ °C}$; $I_{T(RMS)} = 16\text{ A}$; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$; "without snubber" condition; gate open circuit	0.8	-	-	A/ms
		$V_D = 400\text{ V}$; $T_j = 150\text{ °C}$; $I_{T(RMS)} = 16\text{ A}$; $dV_{com}/dt = 1\text{ V}/\mu\text{s}$; gate open circuit	6	-	-	A/ms
t_{gt}	gate-controlled turn-on time	$I_{TM} = 20\text{ A}$; $V_D = 800\text{ V}$; $I_G = 0.1\text{ A}$; $dl_G/dt = 5\text{ A}/\mu\text{s}$	-	2	-	μ s



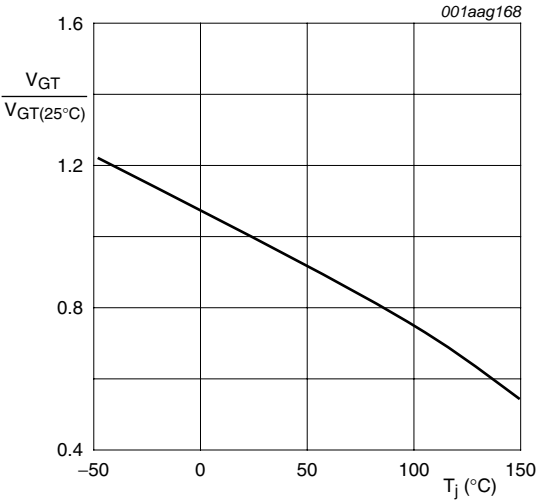


Fig 11. Normalized gate trigger voltage as a function of junction temperature

7. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78

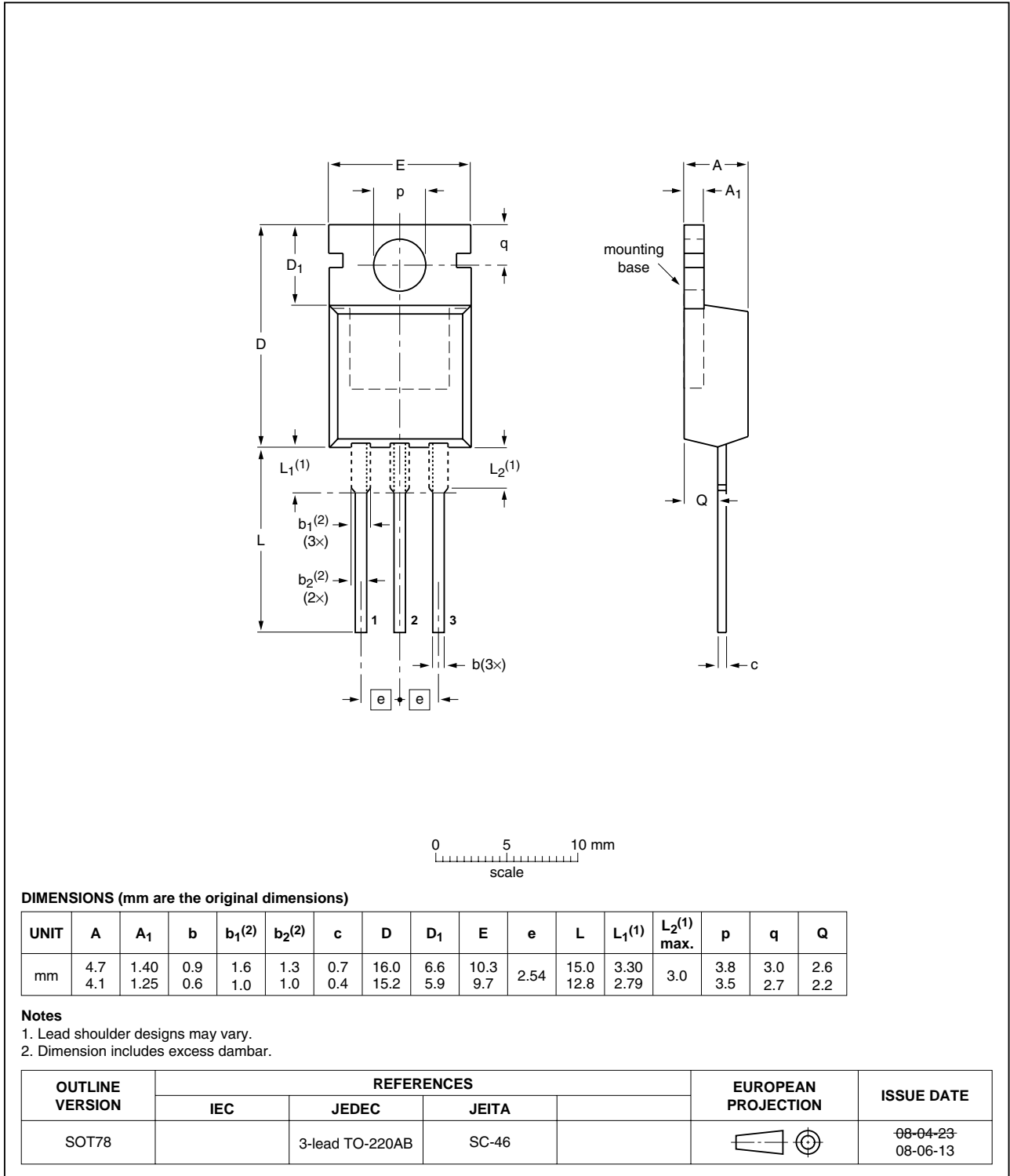


Fig 12. Package outline SOT78 (TO-220AB)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BTA316-800ET_1	20100329	Product data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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